

0.5–10 GHz Low Noise Gallium Arsenide FET

Technical Data

ATF-25170

Features

- **Low Noise Figure:**
0.8 dB Typical at 4 GHz
- **High Associated Gain:**
14.0 dB Typical at 4 GHz
- **High Output Power:**
21.0 dBm Typical $P_{1\text{dB}}$ at 4 GHz
- **Hermetic Gold-Ceramic Microstrip Package**

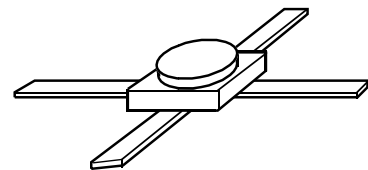
Description

The ATF-25170 is a high performance gallium arsenide Schottky-barrier-gate field effect transistor

housed in a hermetic, high reliability package. Its noise figure makes this device appropriate for use in low noise amplifiers operating in the 0.5-10 GHz frequency range.

This GaAs FET device has a nominal 0.3 micron gate length using airbridge interconnects between drain fingers. Total gate periphery is 500 microns. Proven gold based metallization systems and nitride passivation assure a rugged, reliable device.

70 mil Package



Electrical Specifications, $T_A = 25^\circ\text{C}$

Symbol	Parameters and Test Conditions	Units	Min.	Typ.	Max.	
NF_O	Optimum Noise Figure: $V_{DS} = 3\text{ V}$, $I_{DS} = 20\text{ mA}$	$f = 4.0\text{ GHz}$	dB		0.8	1.0
		$f = 6.0\text{ GHz}$	dB		1.0	
		$f = 8.0\text{ GHz}$	dB		1.2	
G_A	Gain @ NF_O : $V_{DS} = 3\text{ V}$, $I_{DS} = 20\text{ mA}$	$f = 4.0\text{ GHz}$	dB	13.0	14.0	
		$f = 6.0\text{ GHz}$	dB		11.5	
		$f = 8.0\text{ GHz}$	dB		9.0	
$P_{1\text{dB}}$	Power Output @ 1 dB Gain Compression: $V_{DS} = 5\text{ V}$, $I_{DS} = 50\text{ mA}$	$f = 4.0\text{ GHz}$	dBm		21.0	
$G_{1\text{dB}}$	1 dB Compressed Gain: $V_{DS} = 5\text{ V}$, $I_{DS} = 50\text{ mA}$	$f = 4.0\text{ GHz}$	dB		15.0	
g_m	Transconductance: $V_{DS} = 3\text{ V}$, $V_{GS} = 0\text{ V}$		mmho	50	80	
I_{DSS}	Saturated Drain Current: $V_{DS} = 3\text{ V}$, $V_{GS} = 0\text{ V}$		mA	50	100	150
V_P	Pinch-off Voltage: $V_{DS} = 3\text{ V}$, $I_{DS} = 1\text{ mA}$		V	-3.0	-2.0	-0.8

ATF-25170 Absolute Maximum Ratings

Symbol	Parameter	Units	Absolute Maximum ^[1]
V _{DS}	Drain-Source Voltage	V	+7
V _{GS}	Gate-Source Voltage	V	-4
V _{GD}	Gate-Drain Voltage	V	-8
I _{DS}	Drain Current	mA	I _{DSS}
P _T	Power Dissipation ^[2,3]	mW	450
T _{CH}	Channel Temperature	°C	175
T _{STG}	Storage Temperature	°C	-65 to +175

Thermal Resistance: $\theta_{jc} = 300^{\circ}\text{C}/\text{W}$; T_{CH} = 150°C
Liquid Crystal Measurement: 1 μm Spot Size^[4]

Notes:

1. Permanent damage may occur if any of these limits are exceeded.
2. T_{MOUNTING SURFACE} = 25°C.
3. Derate at 3.3 mW/°C for T_{MOUNTING SURFACE} > 40°C.
4. The small spot size of this technique results in a higher, though more accurate determination of θ_{jc} than do alternate methods. See MEASUREMENTS section for more information.

ATF-25170 Noise Parameters: V_{DS} = 3 V, I_{DS} = 20 mA

Freq. GHz	NF _O dB	Γ _{opt}		R _N /50
		Mag	Ang	
1.0	0.6	.89	24	.78
2.0	0.7	.77	50	.53
4.0	0.8	.63	105	.33
6.0	1.0	.66	147	.06
8.0	1.2	.62	-159	.11

ATF-25170 Typical Performance, T_A = 25°C

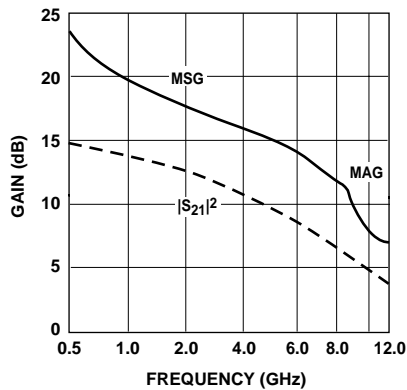


Figure 1. Insertion Power Gain, Maximum Available Gain and Maximum Stable Gain vs. Frequency.
V_{DS} = 3 V, I_{DS} = 20 mA.

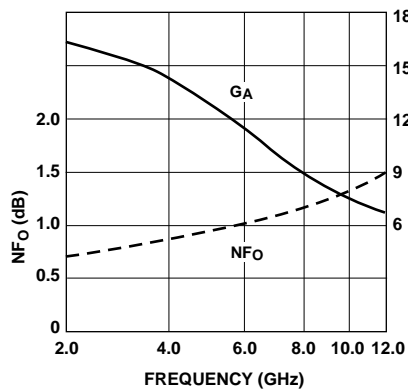


Figure 2. Optimum Noise Figure and Associated Gain vs. Frequency.
V_{DS} = 3V, I_{DS} = 20 mA.

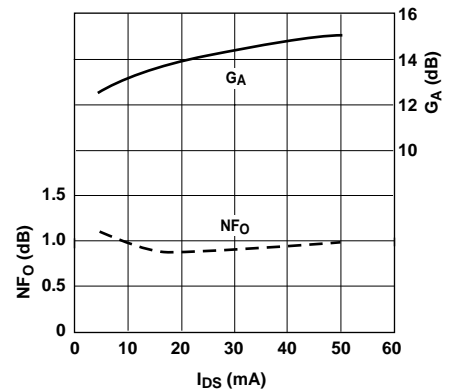


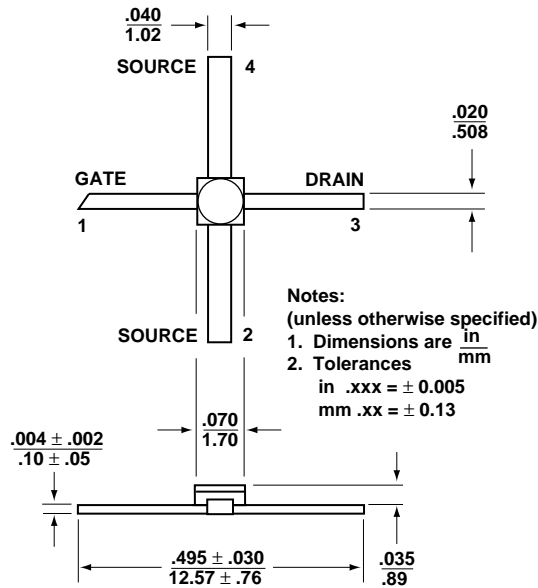
Figure 3. Optimum Noise Figure and Associated Gain vs. I_{DS}.
V_{DS} = 3V, f = 4.0 GHz.

Typical Scattering Parameters, Common Emitter, $Z_0 = 50 \Omega$, $T_A = 25^\circ\text{C}$, $V_{DS} = 3\text{V}$, $I_{DS} = 20\text{mA}$

Freq. GHz	S_{11}		dB	S_{21}		dB	S_{12}		S_{22}	
	Mag.	Ang.		Mag.	Ang.		Mag.	Ang.	Mag.	Ang.
0.5	.98	-23	13.6	4.80	160	-32.8	.023	76	.50	-23
1.0	.96	-38	13.0	4.46	147	-23.6	.037	67	.48	-30
2.0	.88	-66	11.5	3.75	121	-23.6	.066	50	.44	-45
3.0	.80	-86	10.2	3.23	102	-21.8	.081	41	.41	-55
4.0	.77	-106	9.3	2.93	82	-19.7	.103	28	.38	-65
5.0	.71	-127	8.5	2.66	62	-18.6	.118	17	.35	-78
6.0	.65	-149	7.9	2.47	42	-17.7	.130	6	.30	-93
7.0	.60	-173	7.3	2.33	24	-16.5	.149	-4	.26	-111
8.0	.56	161	6.8	2.20	5	-15.8	.162	-16	.22	-134
9.0	.56	136	6.2	2.05	-14	-15.1	.175	-26	.21	-166
10.0	.55	118	5.4	1.87	-31	-15.0	.178	-35	.21	173
11.0	.53	108	4.9	1.76	-46	-14.9	.180	-42	.22	164
12.0	.53	95	4.7	1.71	-62	-14.8	.183	-52	.23	159

A model for this device is available in the DEVICE MODELS section.

70 mil Package Dimensions



This datasheet has been download from:

www.datasheetcatalog.com

Datasheets for electronics components.